

SPICE Modeling using two Picotest M3500A 6½ Digit Multimeters

I was thinking about how a typical engineer would go about creating a SPICE model for a simple diode. This seems like a pretty basic requirement for most of us, at least those of us in power electronics though it is equally important for low frequency RF applications, like diode multipliers. I came up with a few possibilities. One possibility is to see if the diode manufacturer provides a SPICE model, and cross our fingers hoping it's a good model. We would still want to verify the model anyway, so we still need to make the measurement (yes, really. Never trust an unverified model). A second possibility is to use sophisticated equipment, like Agilent IC-Cap, but most of us don't have a budget that allows such a luxury.

We do all have multimeters, so here is my attempt at modeling a diode using two Picotest meters.

The SPICE equation template for the forward conduction of a diode is expressed as

$$V_f(ID) = \ln\left(\frac{ID+IS}{IS}\right) * \frac{kT}{q} * N + ID * RS \quad \text{Eq 1}$$

IS, N and RS are the three primary SPICE parameters controlling the forward conduction of a diode. These refer to Saturation current, Emission Coefficient and Series Resistance respectively.

$k=1.38*10^{-23}$ Boltzmann's Constant
 $q=1.60*10^{-19}$ Electron Charge
T= Temperature in degrees Kelvin

If the measurements are made at relatively low current, then the resistive term becomes insignificant and we can neglect it, simplifying the equation to

$$V_f(ID) = \ln\left(\frac{ID+IS}{IS}\right) * \frac{kT}{q} * N \quad \text{Eq 2}$$

This results in two unknowns, IS and N. If two measurements of V_f are made at two different operating currents, and if the temperature of the measurement is known, then we can define N in two steps as shown in Eq 3 and Eq 4.

$$V_{fI2} - V_{fI1} = \ln\left(\frac{I2}{I1}\right) * \frac{kT}{q} * N \quad \text{Eq 3}$$

Rearranging things a bit and solving for N yields

$$N = \frac{Vf_{I2} - Vf_{I1}}{\ln\left(\frac{I2}{I1}\right) * \frac{kT}{q}} \quad \text{Eq 4}$$

Fortunately, each M3500 is capable of two, simultaneous measurements, so that the diode voltage and the measurement temperature can be obtained using a single DMM.

A second DMM is used as a precision current source, making use of the measurement scheme for resistance, which forces a current into the resistor being tested while measuring the voltage across it. We will not measure the resistance, but we will use the second meter as a current source.

The 10KΩ scale uses a test current of 100uA, while the 1KΩ scale uses a test current of 1mA. Using these two measurement scales along with the temperature measurement, in degrees C, results in Eq 5

$$N = \frac{Vf_{I2} - Vf_{I1}}{\ln\left(\frac{1mA}{100uA}\right) * \frac{k(T+273)}{q}} \quad \text{Eq 5}$$

Equation 5 can be solved, since all of the terms are known.

With N solved, IS can be calculated by substitution of either of the two voltage measurements into equation 2, rearranging and solving for IS as shown in Eq 6.

$$IS = \frac{ID}{e^{\frac{Vf * q}{k * (T+273) * N} - 1}} \quad \text{Eq 6}$$

Example diode measurement goes here

As an example, I used a simple 1N4148 diode resulting in the following measurements

	Vf	Test Current
10KΩ scale		100uA
1KΩ scale		1mA
Temperature		

Also need schematic and/or picture of the test setup

Solving for RS is a bit more difficult as it requires a measurement at a 3rd, much higher current. The higher current will tend to heat the diode, so it must be a very fast measurement. If we can make such a measurement (which I hope to figure out for another BLOG) then the RS term can be calculated as

$$RS = Vf_{I3} * q - \ln\left(\frac{I3+IS}{IS}\right) * \frac{k*(T+273)}{q} * N \quad \text{Eq 7}$$

If the datasheet includes a high current measurement, it isn't ideal but we can use it for the 3rd measurement.

If readers find this interesting, I'll try to come up with a few more ideas on how to use Picotest equipment to solve some of these interesting challenges.